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Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

**Listing of Claims**:

Claims 1-3 (cancelled).

Claim 4 (currently amended): The display of claim 17, wherein in order to install said control circuit in a control circuit accommodation portion of said TFT first substrate, said control circuit accommodation portion is made thinner than other portions of said TFT first substrate.

Claim 5 (cancelled).

Claim 6 (previously presented): The display of claim 17, wherein said control circuit is packed over said first substrate by COG (chip-on-glass) technology.

Claims 7-12 (cancelled).

Claim 13 (previously presented): The method of claim 24, further comprising the step of thinning a portion of said counter substrate which is located opposite to a control circuit for controlling said driver circuit made up of said driver TFTs, to install said control circuit.

Claim 14 (previously presented): The method of claim 24, wherein said control circuit is packed over said first substrate by COG (chip-on-glass) technology.

Claims 15-16 (cancelled).

Claim 17 (currently amended): An active matrix liquid crystal display comprising:

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a plurality of pixel TFTs arranged in rows and columns over a first substrate and arrayed in a matrix;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said counter substrate;

a sealing material sealing over around said liquid crystal material and provided between said first substrate and said counter substrate; and

## a driver TFT provided over said first substrate; and

a control circuit comprising a control circuit chip provided under and in contact with said sealing material, said control circuit provided over said first substrate <u>for controlling</u> said driver TFT.

Claims 18-20 (cancelled).

Claim 21 (currently amended): An active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a first substrate and arrayed in a matrix;

a bus line provided over said first substrate and connected with at least one of said pixel TFTs;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said counter substrate:

a sealing material sealing over around said liquid crystal material and provided between said first substrate and said counter substrate; and

## a driver TFT provided over said first substrate; and

a control circuit comprising a control circuit chip provided under and in contact with said sealing material, said control circuit provided over said first substrate <u>for controlling</u> said driver TFT.

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Claim 22 (currently amended): An active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a first substrate and arrayed in a matrix;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said counter substrate;

a sealing material sealing over around said liquid crystal material and provided between said first substrate and said counter substrate, said sealing material being provided outside at least said pixel TFTs; and

## a driver TFT provided over said first substrate; and

a control circuit comprising a control circuit chip provided under and in contact with said sealing material, said control circuit provided over said first substrate for controlling said driver TFT.

Claim 23 (currently amended): An active matrix liquid crystal display comprising: a plurality of pixel TFTs arranged in rows and columns over a first substrate and

arrayed in a matrix;

a bus line provided over said first substrate and connected with at least one of said pixel TFTs;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said counter substrate;

a sealing material sealing over around said liquid crystal material and provided between said first substrate and said counter substrate, said sealing material being provided outside at least said pixel TFTs; and

a driver TFT provided over said first substrate; and

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a control circuit comprising a control circuit chip provided under and in contact with said sealing material, said control circuit provided over said first substrate for controlling said driver TFT.

Claim 24 (currently amended): A method of fabricating an active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a first substrate and arrayed in a matrix;

a bus line provided over said first substrate and connected with at least one of said pixel TFTs;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said counter substrate;

a sealing material sealing over around said liquid crystal material and provided between said first substrate and said counter substrate and outside at least said pixel TFTs; and

a driver TFT provided over said first substrate; and

a control circuit comprising a control circuit chip provided under and in contact with said sealing material, said control circuit provided over said first substrate <u>for controlling</u> said driver TFT,

said method comprising:

cutting said first substrate and said counter substrate outside said sealing material having said control circuit under and in contact with said sealing material.

Claim 25 (currently amended): A method of fabricating an active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a first substrate and arrayed in a matrix;

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a bus line provided over said first substrate and connected with at least one of said

pixel TFTs;

a counter substrate located opposite to said first substrate;

a layer of a liquid crystal material provided between said first substrate and said

counter substrate;

a sealing material sealing over around said liquid crystal material and provided

between said first substrate and said counter substrate; and

a driver TFT provided over said first substrate; and

a control circuit comprising a control circuit chip provided under and in contact

with said sealing material, said control circuit provided over said first substrate for controlling

said driver TFT,

said method comprising:

cutting said first substrate and said counter substrate outside said sealing material

having said control circuit under and in contact with said sealing material.

Claims 26-29 (cancelled).

Claim 30 (currently amended): The display of claim 21, wherein in order to install said

control circuit in a control circuit accommodation portion of said TFT first substrate, said

counter substrate has a thinned portion located opposite to said control circuit accommodation

portion.

Claim 31 (previously presented): The display of claim 21, wherein said control circuit is

packed over said first substrate by COG (chip-on-glass) technology.

Claims 32-34 (cancelled).

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Claim 35 (currently amended): The display of claim 22, wherein in order to install said control circuit in a control circuit accommodation portion of said TFT first substrate, said counter substrate has a thinned portion located opposite to said control circuit accommodation portion.

Claim 36 (previously presented): The display of claim 22, wherein said control circuit is packed over said first substrate by COG (chip-on-glass) technology.

Claims 37-39 (cancelled).

Claim 40 (currently amended): The display of claim 23, wherein in order to install said control circuit in a control circuit accommodation portion of said TFT first substrate, said counter substrate has a thinned portion located opposite to said control circuit accommodation portion.

Claim 41 (previously presented): The display of claim 23, wherein said control circuit is packed over said first substrate by COG (chip-on-glass) technology.

Claim 42 (previously presented): The method of claim 25, wherein said cutting step is carried out in such a way that said cut side edges to which said nonconductive or weakly conductive material is applied or adhesively bonded are parallel or vertical to a direction of array of said pixel TFTs.

Claim 43 (cancelled).

Claim 44 (previously presented): The method of claim 25, further comprising the step of thinning a portion of said counter substrate which is located opposite to said control circuit, to install said control circuit.

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Claims 45-60 (cancelled).

Claim 61 (currently amended): A semiconductor device comprising:

a pixel TFT provided over a first substrate comprising a glass;

a channel formation region provided in a semiconductor film provided over said first substrate;

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween, said pixel TFT comprising said channel formation region and said gate electrode and said gate insulating film;

a counter substrate located opposite to said first substrate;

a bus line provided over said first substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said first substrate;

a sealing material provided between said first substrate and said counter substrate; and

a nonconductive material applied to a side edge of said counter substrate and said side edge of said first substrate and said part of said bus line, said nonconductive material applied to three sides of said first substrate and three sides of said counter substrate,

wherein said nonconductive material is provided on an outer side of said sealing material, and

wherein said gate insulating film has a thickness of 500 to 2000 Å

wherein said nonconductive material is not applied to one side of said first substrate and is not applied to one side of said counter substrate.

Claim 62 (currently amended): A semiconductor device comprising:

a pixel TFT provided over a first substrate comprising a glass;

a channel formation region provided in a semiconductor film provided over said first substrate;

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a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween, said pixel TFT comprising said channel formation region and said gate electrode and said gate insulating film;

a counter substrate located opposite to said first substrate;

a bus line provided over said first substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said first substrate;

a sealing material provided between said first substrate and said counter substrate; and

a weakly conductive material applied to a side edge of said counter substrate and said side edge of said first substrate and said part of said bus line, said weakly conductive material applied to three sides of said first substrate and three sides of said counter substrate,

wherein said weakly conductive material is provided on an outer side of said sealing material, and

wherein said gate insulating film has a thickness of 500 to 2000 Å

wherein said weakly conductive material is not applied to one side of said first substrate and is not applied to one side of said counter substrate.

Claim 63 (currently amended): A semiconductor device comprising:

a pixel TFT provided over a first substrate comprising a glass;

a channel formation region provided in a semiconductor film provided over said first substrate;

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween, said pixel TFT comprising said channel formation region and said gate electrode and said gate insulating film;

a driver TFT provided over said first substrate;

a counter substrate located opposite to said first substrate;

a bus line provided over said first substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said first substrate;

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a sealing material provided between said first substrate and said counter substrate; and

a nonconductive material applied to a side edge of said counter substrate and said side edge of said first substrate and said part of said bus line, said nonconductive material applied to three sides of said first substrate and three sides of said counter substrate,

wherein said nonconductive material is provided on an outer side of said sealing material, and

wherein said gate insulating film has a thickness of 500 to 2000 Å

wherein said nonconductive material is not applied to one side of said first substrate and is not applied to one side of said counter substrate.

Claim 64 (currently amended): A semiconductor device comprising:

a pixel TFT provided over a first substrate comprising a glass;

a channel formation region provided in a semiconductor film provided over said first substrate;

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween, said pixel TFT comprising said channel formation region and said gate electrode and said gate insulating film;

a driver TFT provided over said first substrate;

a counter substrate located opposite to said first substrate;

a bus line provided over said first substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said first substrate;

a sealing material provided between said first substrate and said counter substrate; and

a weakly conductive material applied to a side edge of said counter substrate and said side edge of said first substrate and said part of said bus line, said weakly conductive material applied to three sides of said first substrate and three sides of said counter substrate,

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wherein said weakly conductive material is provided on an outer side of said sealing material, and

wherein said gate insulating film has a thickness of 500 to 2000 Å

wherein said weakly conductive material is not applied to one side of said first substrate and is not applied to one side of said counter substrate.

Claims 65-68 (cancelled).

Claim 69 (previously presented): The display of claim 61 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said first substrate.

Claim 70 (previously presented): The display of claim 62 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said first substrate.

Claim 71 (previously presented): The display of claim 63 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said first substrate.

Claim 72 (previously presented): The display of claim 64 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said first substrate.